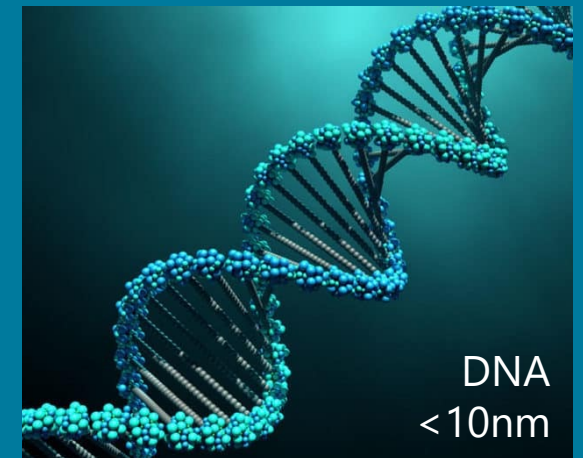
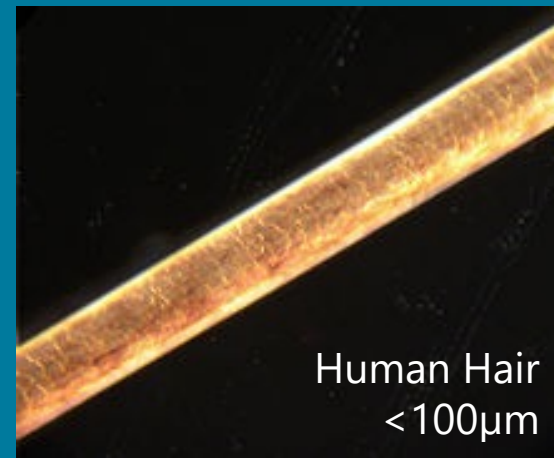


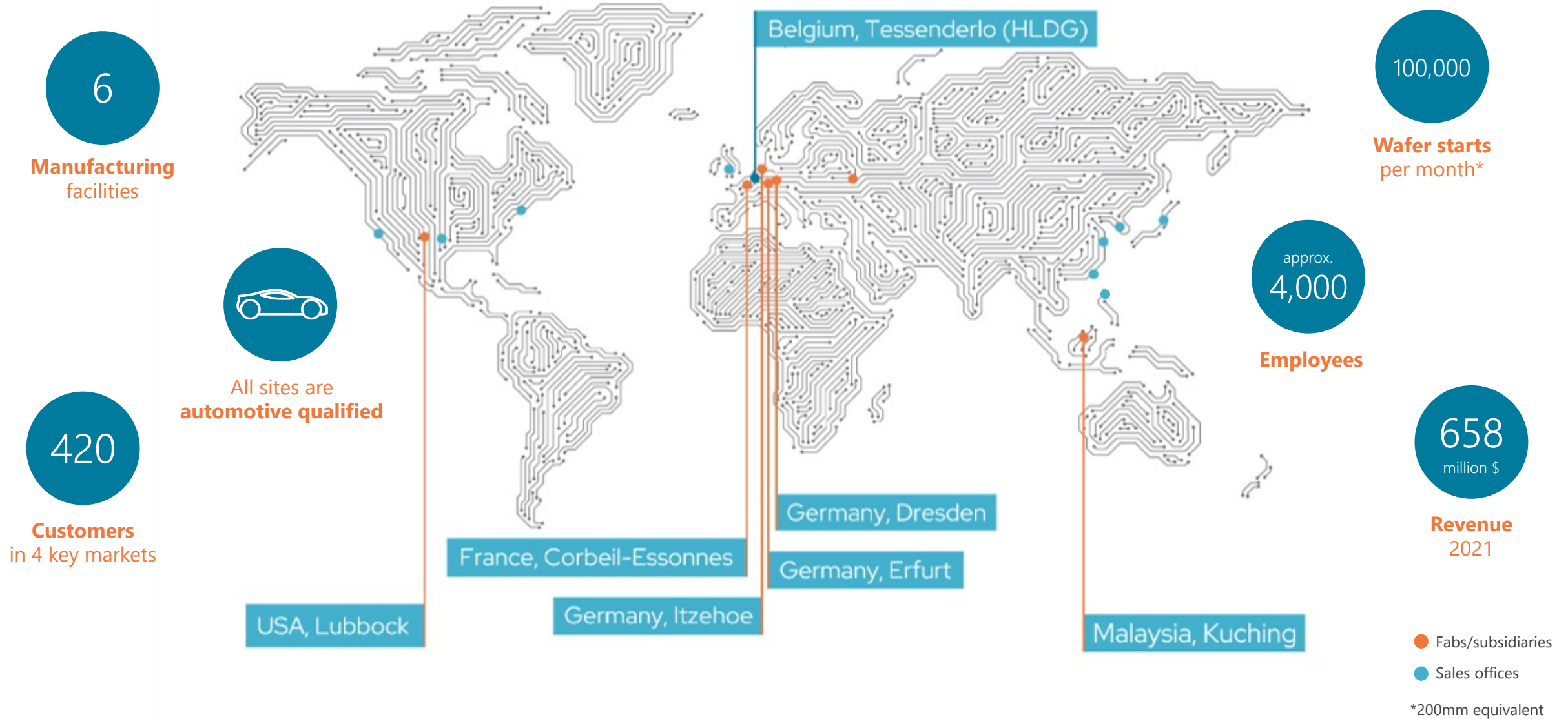
Potential and Challenges of **NEMS** – *A Foundry View*

Dr. Stefan Ernst
Business & Strategy MEMS
Bristol, 30-June, 2022



X-FAB at a glance

30 years of
xfab



Serving the strongest growing end markets



Automotive

- › Electrification
- › Improved safety
- › ADAS
- › Environmental protection
- › Connected cars and services

Industrial

- › Power management
- › Factory automation
- › Intelligent drive and motor control
- › Smart buildings and cities



Medical

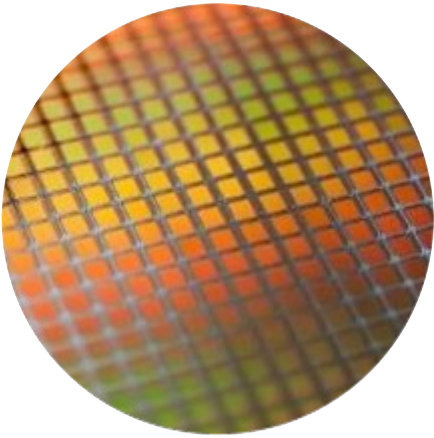
- › Personal medical devices
- › Medical equipment
- › Lab-on-a-chip

Consumer, Communications, Computer

- › Smart home
- › Connectivity
- › Communication
- › Appliances and HVAC

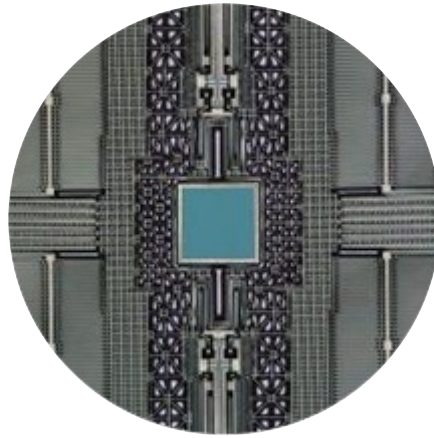


ADAS = Advanced Driver Assistance System, HVAC = Heating, Ventilation and Air Conditioning



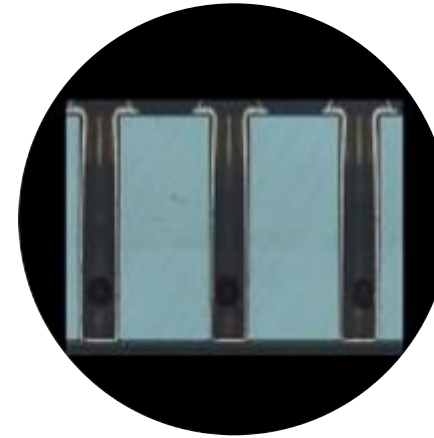
CMOS & SOI

13 process families with over 450 options



MEMS

MEMS with or without integrated CMOS



Heterogeneous integration

3D integration and wafer level package solutions



SiC & GaN

Processing technologies for WBG
6" SiC & 8" GaN-on-Si

CMOS & SOI offering

Large portfolio of process technologies & IP

X-FAB process portfolio and features

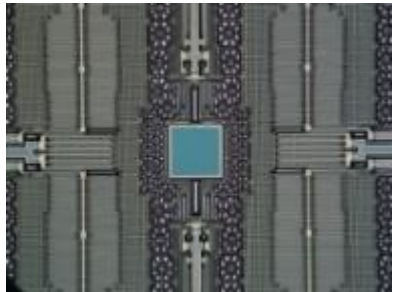
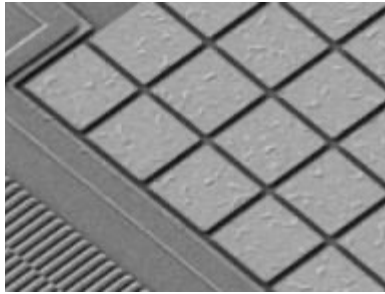
Technology node ↓	1.0 μm	Digital	Analog M/S	High Voltage	NVM		Opto	SOI	High Temp	MEMS
	0.8 μm	Digital	Analog M/S	High Voltage	NVM		Opto			
	0.6 μm	Digital	Analog M/S	High Voltage	NVM	RF	Opto	SOI	High Temp	MEMS
	0.35 μm	Digital	Analog M/S	High Voltage	NVM	RF	Opto		High Temp	MEMS
	0.25 μm	Digital	Analog M/S		NVM					
	0.18 μm	Digital	Analog M/S	High Voltage	NVM	RF	Opto	SOI	High Temp	
	0.13 μm	Digital	Analog M/S		NVM	RF		SOI		

M/S = mixed-signal, NVM = non volatile memory, RF = radio frequency, SOI = silicon on insulator, MEMS = microelectromechanical systems, SiC = silicon carbide

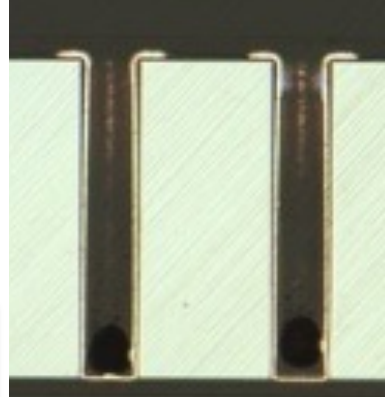
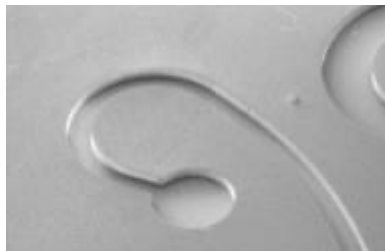


MEMS Technology Pillars + Application view

Sensors: Pressure, inertial, thermopile



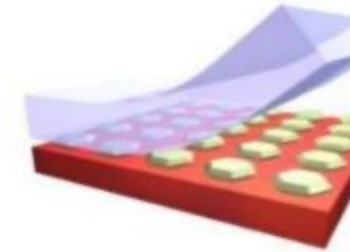
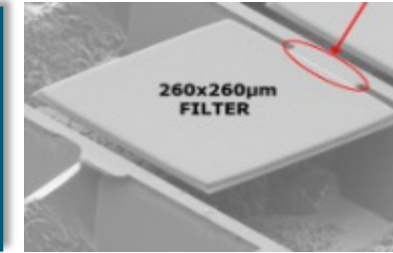
Functional surfaces & fluidic primitive devices



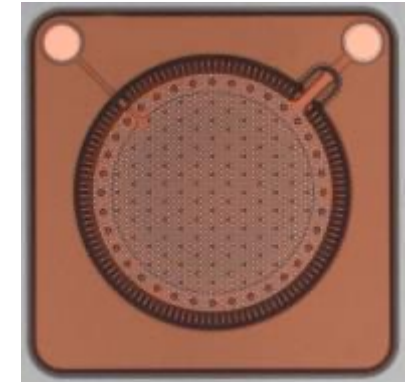
Wafer level integration and packaging



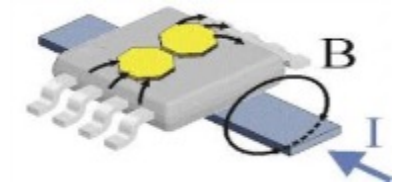
Thin-film Piezo-electric materials



Heterogeneous integration – Micro Transfer Printing (μ TP)

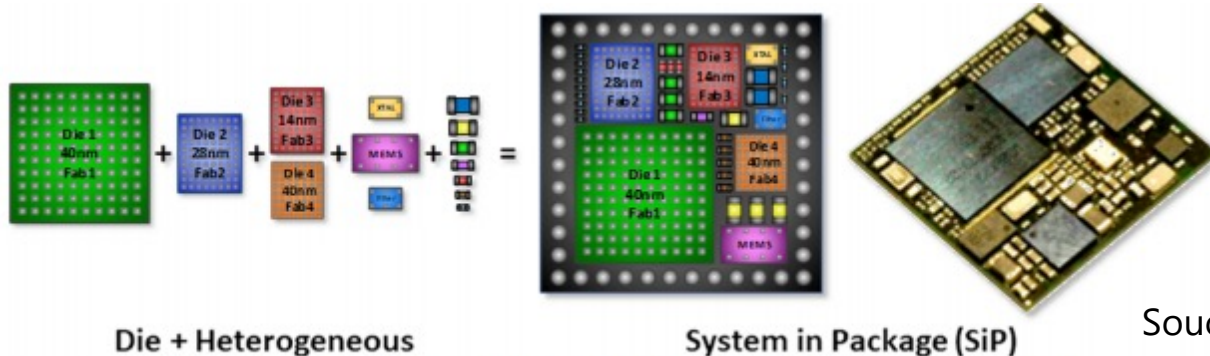
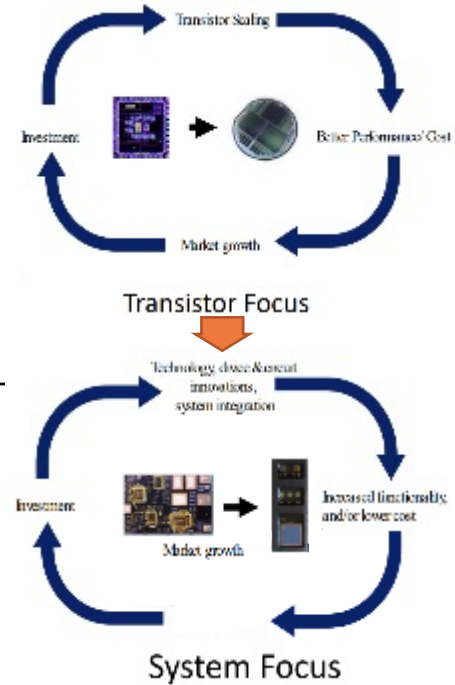


Customer specific processes



MtM Scaling. Heterogeneous Integration

- > Semi industry experiences a paradigm shift from Moore's Law scaling to MtM evolution through **advances in system integration** in response to market applications
 - Mainly driven by High-Performance computing/data centers, IoT, Mobile, **but also arrived in Medical/Health, Automotive and Production** (c.f. HIR 2020 Edn.)
- > **Heterogeneous Integration** (Source ITRS):
 - integration of separately manufactured components into a higher-level assembly (System in Package – SiP) that, in the aggregate, provides enhanced functionality and improved operating characteristics.
 - Components: any unit, whether individual die, MEMS device, passive component and assembled package or sub-system.
- > **The Three Levels of Heterogeneous Integration**
 - **Chip/Device Level** – **System Level** – Software / Application Level. (J. Alvarez, Intel PSG CTO, February 20),

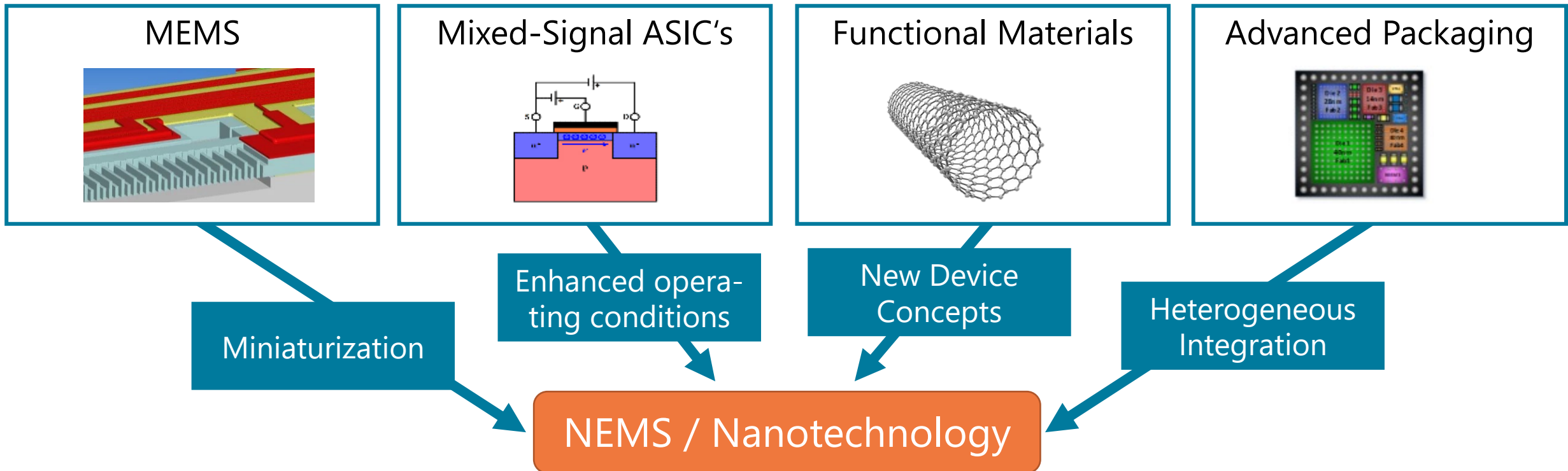
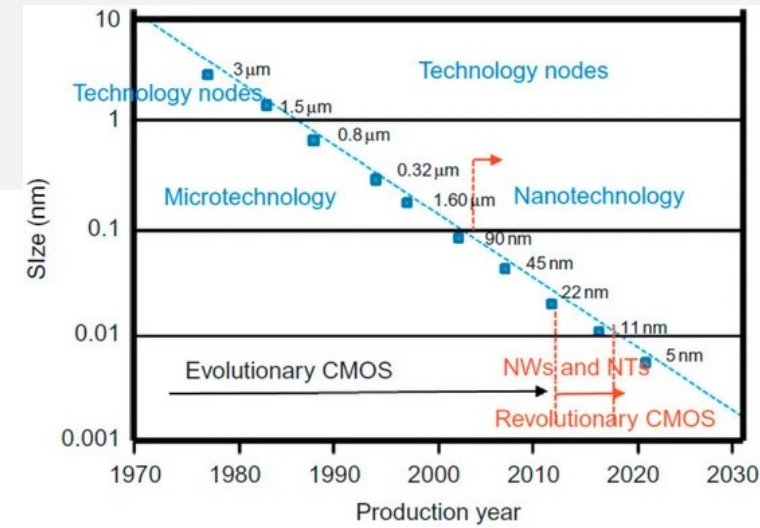


Source: ASE Group



Why NEMS?

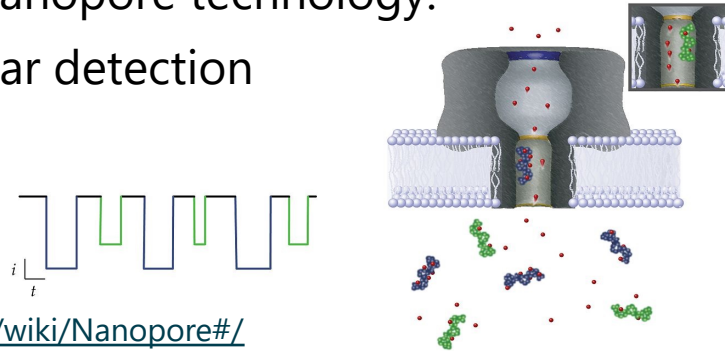
- > integrating electrical and mechanical functionality on the nanoscale
- > first demonstration of VLSI NEMS device by IBM in 2000: "MILLIPEDE", array of AFM tips which can heat/sense a deformable substrate → memory device.



NEMS & Nanotechnology for Biomedical Applications

Nano-structured materials to detect biological features on molecular scale

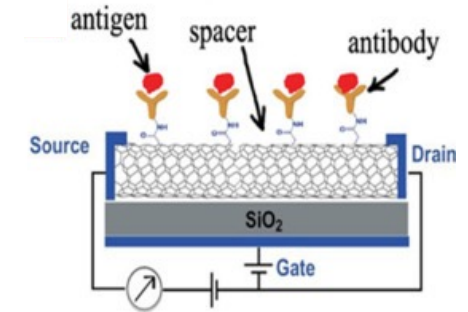
- (Solid-State) Nanopore technology: single-molecular detection



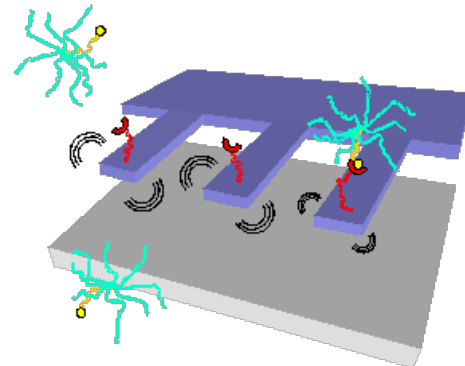
<https://en.wikipedia.org/wiki/Nanopore#/>

- Low-dimensional materials: enhanced biosensor performance

- 2D: Graphene, TMC's etc
- 1D: Carbon Nanotube (CNT)

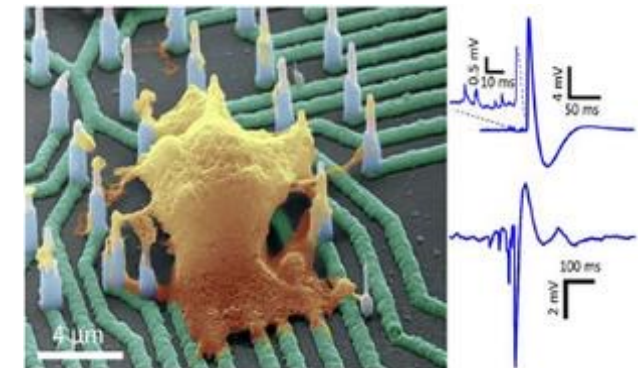


- BioNEMS: extend Chemical Force Microscopy (cantilever-based sensors) to bio-assays



<http://nano.caltech.edu/research/nems-biosensors.html>

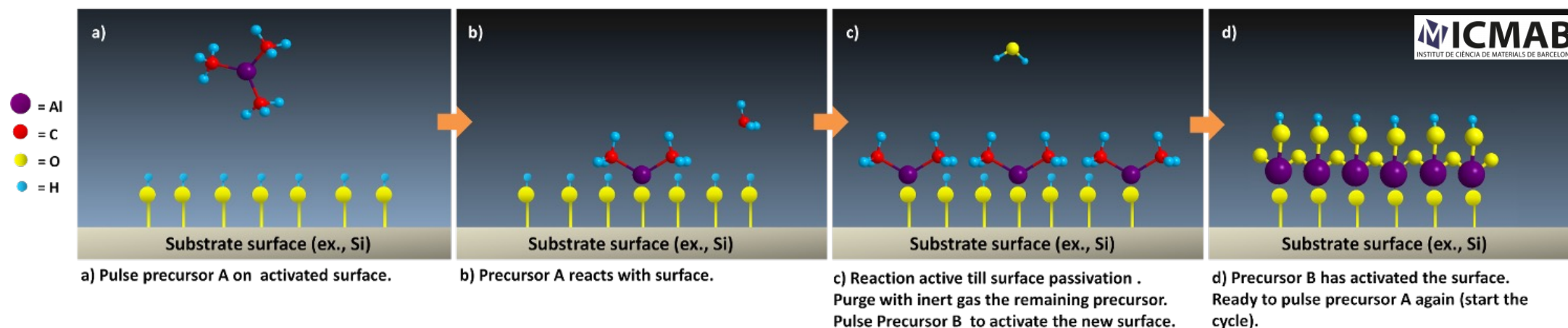
- Nanoelectrode Arrays (NEAs): real-time dynamic analysis on different biological levels (cell, tissue, organ)



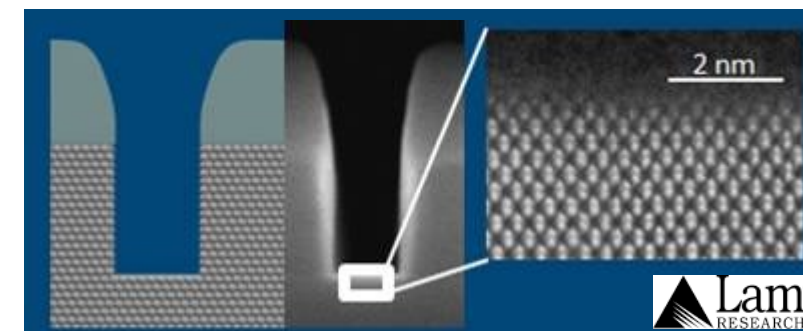
<https://www.frontiersin.org/articles/10.3389/fchem.2020.573865/full>

- > **Atomic Layer Deposition (ALD):** Chemical Vapour-phase Deposition method based on a sequence of (one or more) self-limiting surface reactions, leading to conformal growth of individual monoatomic layers

Example of Al_2O_3 layers grown by trimethylaluminum (TMA) and H_2O

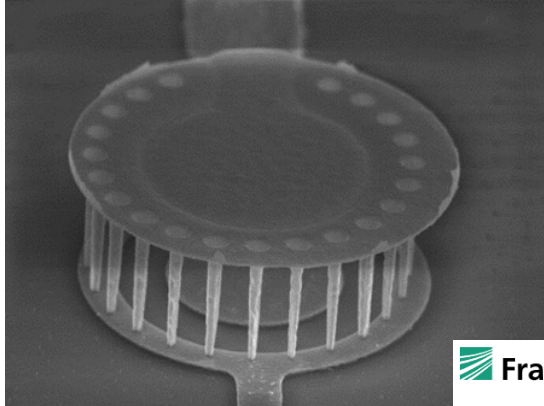


- > **Atomic Layer Etching (ALE):** sequence alternating between self-limiting chemical modification steps which affect only the top atomic layers of the wafer, and etching steps which remove only the chemically-modified areas, allowing the removal of individual atomic layers

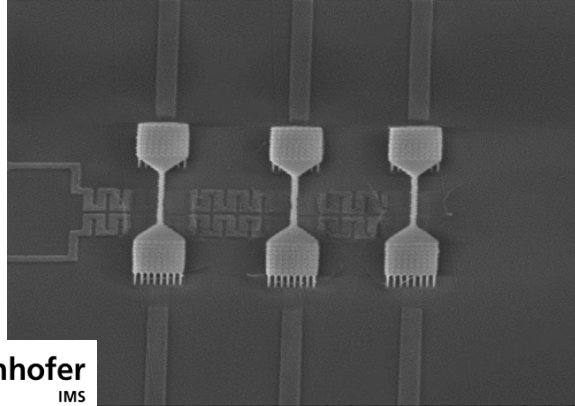


Atomic Layer Deposition - Examples

> Sacrificial Layer Technologies for creation of 3D NEMS



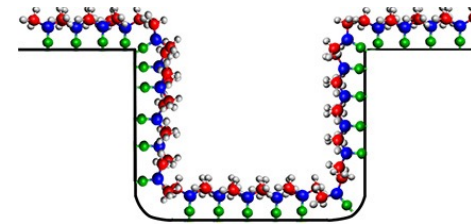
3D-Membrane
(capacitor, micro scale)



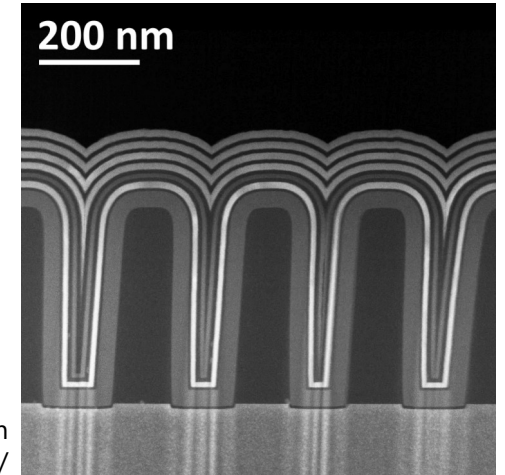
Freestanding Nanowire
(heater, gas sensor)



> Conformal thin-layer deposition (passivation, functional layers)



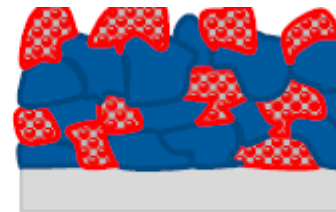
<https://www.atomiclimits.com/imagebase/>



> Nano-structured materials



Nano laminate:
High specific number of Al_2O_3 and ZnO cycles,
deposition of a close layer before starting with
pulsing the second material

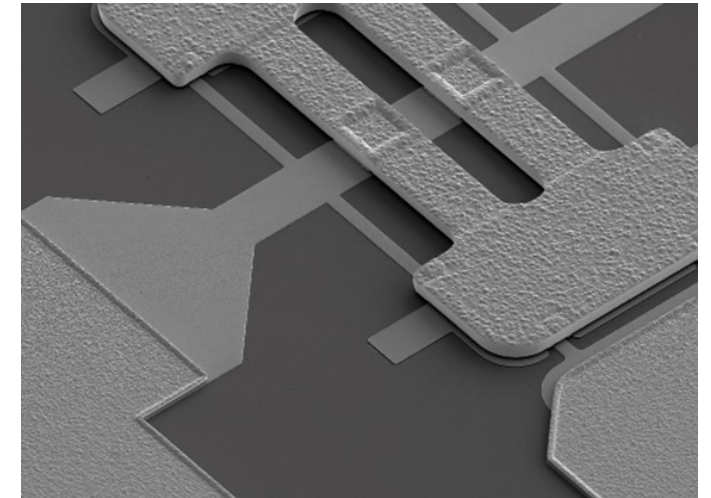


Homogenous mixture:
Low specific number of Al_2O_3 and ZnO cycles,
just nucleation until starting with pulsing the
second material



Advantages of MEMS/NEMS technology for switching application:

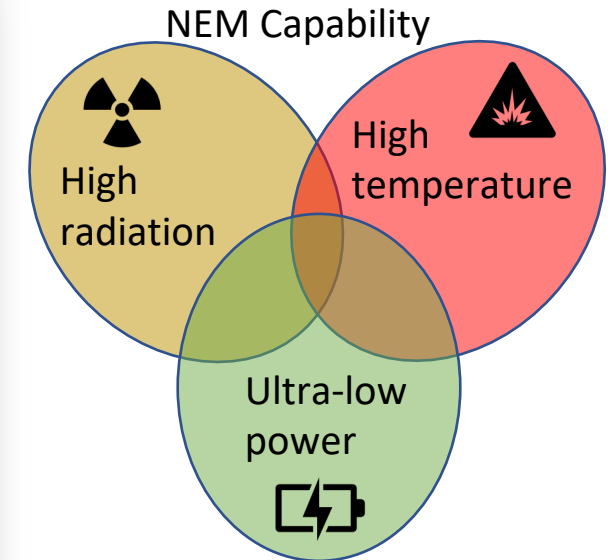
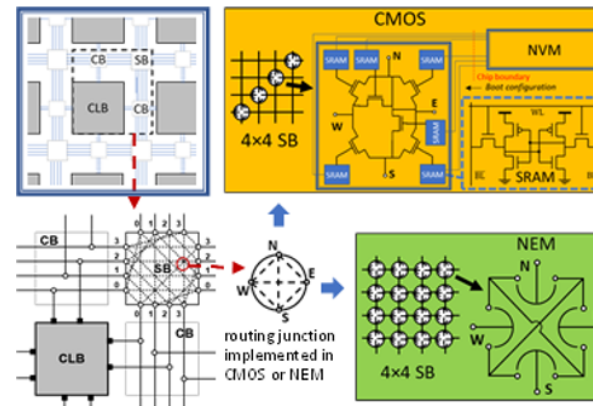
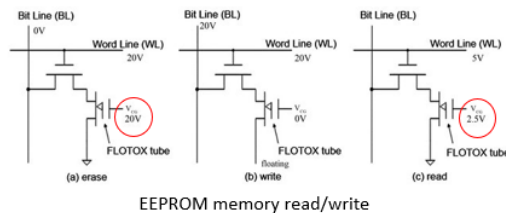
- › Low leakage (IoT -> power gating: extend power source lifetime; low duty-cycle applications)
- › Low power consumption
- › reduced switching losses and parasitics, multiple frequencies on one chip (RF MEMS)
- › Extended operating temperature range
 - CMOS operational up to 175°C -> M/NEMS can extend to 300°C and beyond
 - Reliability: high T over all mission profile
 - Batteries are temperature limited -> replace by super cap
- › High voltage / high power capability: galvanic isolation
 - MEMS Driver, Level Shifter
- › Scalable / CMOS integrable



Source: Menlo Micro / EE World

NEMS and their beneficial characteristics

- Design advantages over CMOS
 - Simpler memory design (one voltage for both reading and programming)
 - Logic and memory use the same technology – powerful platform for edge compute
 - Lower power usage for FPGA implementation of Artificial Neural Networks (ANN)
 - Greater flexibility and simplicity of FPGA switch box
 - “On the fly” ANN level adjustment – no remote memory



Industrialization Challenges

In general (*and related to ZeroAMP*)

A) Process Technology: new Functional materials (*e.g., contact material & design*)

- › Process maturity and compatibility / scalability
- › Performance & Characteristics (*contact resistance, sticky vs. non-sticky contact, ...*)
- › Reliability (*Wear-out, # of cycles*)

→ **in-depth material characterization needed**

- › Process integration
last: High-T compatible metallization
- › Integration into existing manufacturing ecosystem;
Cross Contamination management
- › Process Control / Q-gates



Industrialization (cont'd)

In general (*and related to ZeroAMP*)

B) Application View:

- › System Architecture (*Integration of memory or logics with drive / read-out capable with high T*)
- › Ecosystem for system design and supply chain

C) Commercial Aspects

- Advantages of NEM-based technologies are very specific
 - niche applications challenge economy of scale
- High-volume applications (IoT) require economy of scale
 - significant invest, cost of ownership
- Cost of quality / yield



- NEMS constitute a promising technological approach for a number of applications
 - Efficiency gain for logic, power mgnt, RF, ...
 - Extended operating areas unlock new applications
 - Enhanced sensor architectures
- Still at early stage
 - Challenges of industrialization
 - Time to shape the future:
building a technology roadmap tailored to application needs

This project has received funding from the European Union's Horizon 2020 research and innovation programme under grant agreement No 871740 (ZeroAMP).



30 years of
xfab

Thank you.



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